TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

# 2SC4118

Audio Frequency Low Power Amplifier Applications
Driver Stage Amplifier Applications
Switching Applications

- Excellent hFE linearity: hFE (2) = 25 (min) (VCE = 6 V, IC = 400 mA)
- Complementary to 2SA1588

#### **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	35	V
Collector-emitter voltage	V <sub>CEO</sub>	30	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	IC	500	mA
Base current	ΙΒ	50	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.

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2. EMITTER
USM
3. COLLECTOR

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JEITA

SC-70

TOSHIBA

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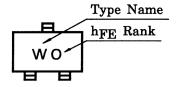
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Weight: 0.006 g (typ.)

operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### Marking





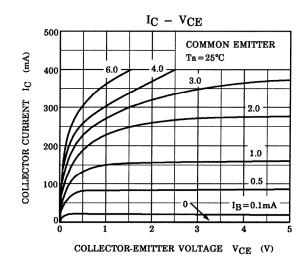
## Electrical Characteristics (Ta = 25°C)

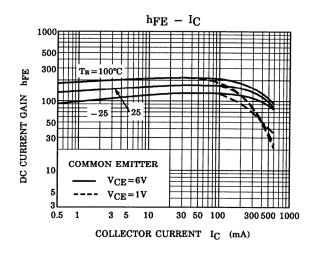
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 35 \text{ V}, I_{E} = 0$	_	_	0.1	μА
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0	_	_	0.1	μА
DC current gain	h <sub>FE (1)</sub> (Note)	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 100 mA	70	_	400	
	h <sub>FE (2)</sub> (Note)	V <sub>CE</sub> = 6 V, I <sub>C</sub> = 400 mA	25	_	_	
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = 100 mA, I <sub>B</sub> = 10 mA	_	0.1	0.25	٧
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 100 mA	_	0.8	1.0	٧
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 6 V, I <sub>C</sub> = 20 mA	_	300	_	MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 6 V, I <sub>E</sub> = 0, f = 1 MHz		7	_	pF

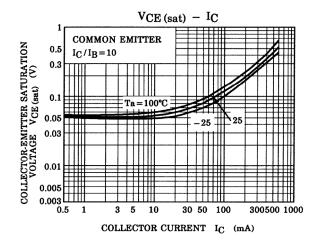
Note:  $h_{FE\ (1)}$  classification O(O): 70~140, Y(Y): 120~240, GR(G): 200~400 ( ) Marking Symbol

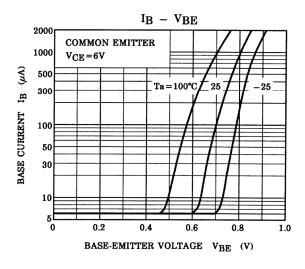
h<sub>FE (2)</sub> classification O: 25 (min), Y: 40 (min), GR: 70 (min)

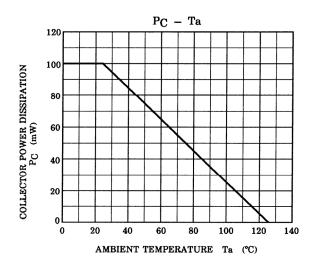
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20070701-EN GENERAL

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